



# ACE7332M

## N-Channel 30-V (D-S) MOSFET

### Description

The ACE7332M uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a kelvin connection to the source, which may be used to bypass the source inductance.

### Key Features

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

### Features

- $V_{DS}(V)=30V$
- $I_D=15A$  ( $V_{GS}=10V$ )
- $R_{DS(ON)} < 8.5m\Omega$  ( $V_{GS}=10V$ )
- $R_{DS(ON)} < 13m\Omega$  ( $V_{GS}=4.5V$ )

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
30	13 @ $V_{GS} = 10V$	14
	18 @ $V_{GS} = 4.5V$	12

### Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current (Continuous) *AC	$I_D$	$T_A=25^\circ C$	15
		$T_A=70^\circ C$	12
Drain Current (Pulse) *B	$I_{DM}$	50	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	3.5
		$T_A=70^\circ C$	2
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	t $\leq$ 10 sec	35
		Steady State	81

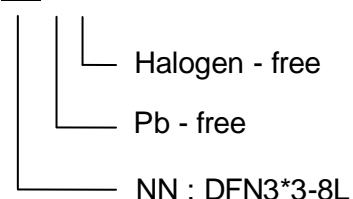
### Packaging

DFN3x3-8L



### Type Ordering information

ACE7332M XX + H





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### Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max	Unit
<b>Static</b>						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 V, V_{GS} = \pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 V, V_{GS} = 0 V$			1	uA
		$V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	20			A
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(ON)}$	$V_{GS} = 10 V, I_D = 11 A$			13	mΩ
		$V_{GS} = 4.5 V, I_D = 8.8 A$			18	
Forward Transconductance <sup>a</sup>	$g_{FS}$	$V_{DS} = 15 V, I_D = 11 A$		25		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.6 A, V_{GS} = 0 V$		0.74		V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 11 A$		25		nC
Gate-Source Charge	$Q_{gs}$			11		
Gate-Drain Charge	$Q_{gd}$			17		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 15 V, R_L = 1.4 \Omega, I_D = 11 A, V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		15		ns
Rise Time	$t_r$			13		
Turn-Off Delay Time	$t_{d(off)}$			100		
Fall Time	$t_f$			54		
Input Capacitance	$C_{iss}$	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		1456		pF
Output Capacitance	$C_{oss}$			231		
Reverse Transfer Capacitance	$C_{rss}$			198		

Note:

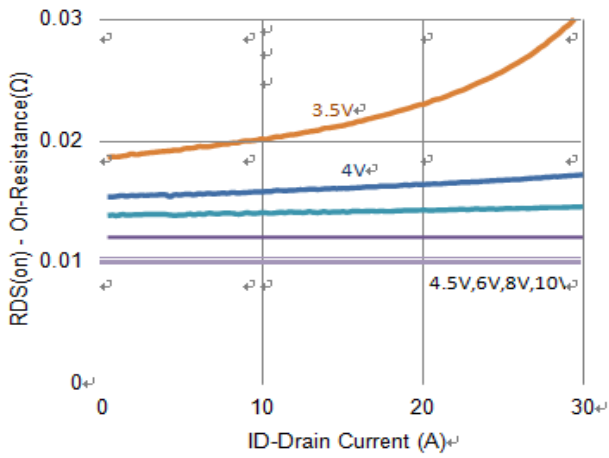
- Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing



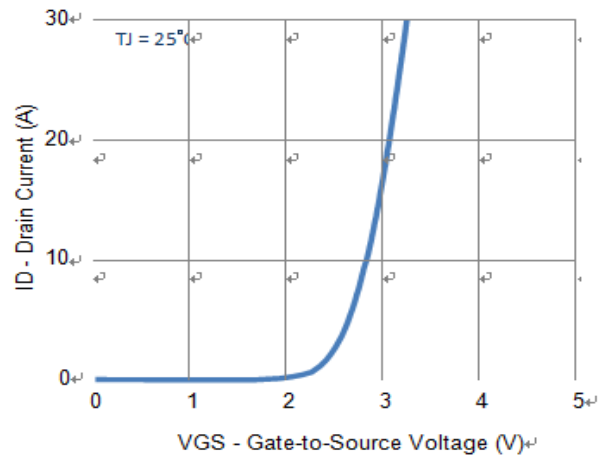
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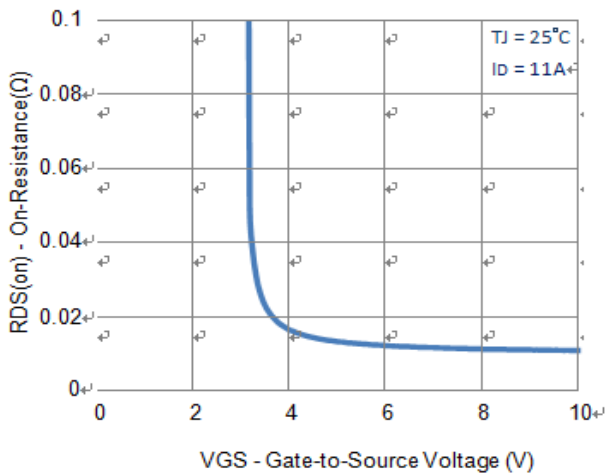
### Typical Performance Characteristics



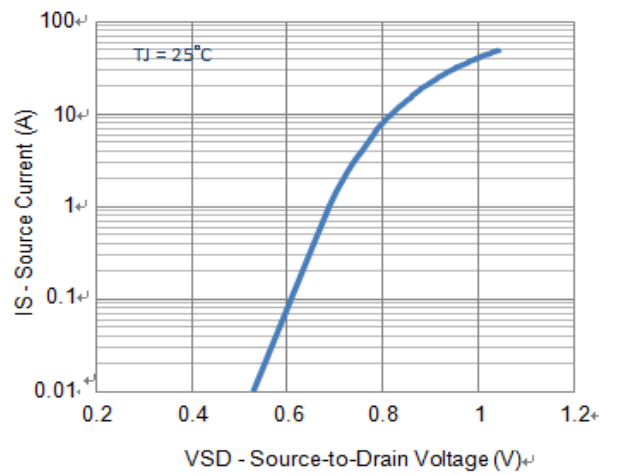
1. On-Resistance vs. Drain Current



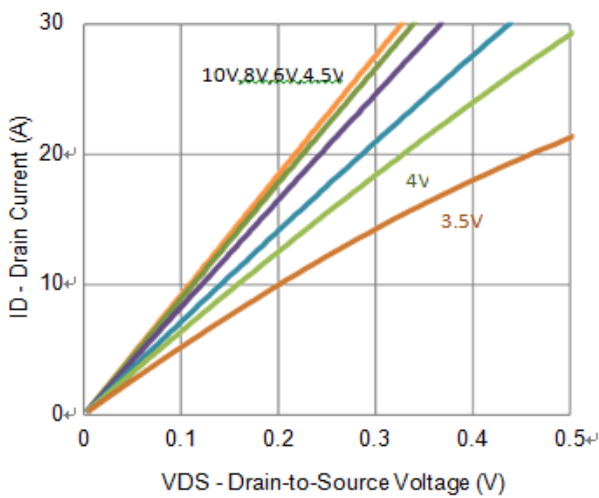
2. Transfer Characteristics



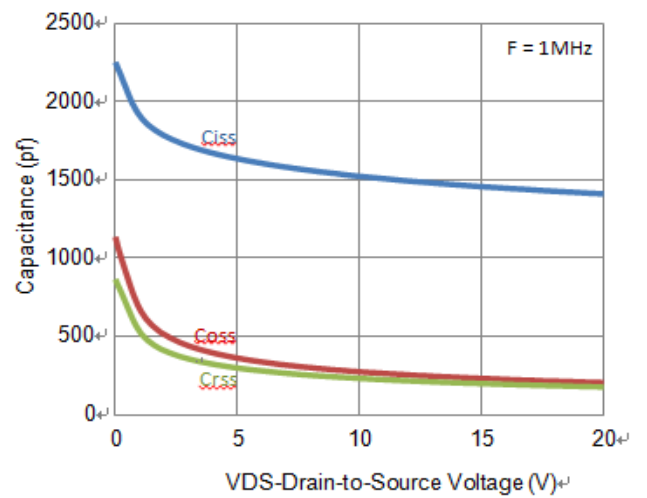
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics

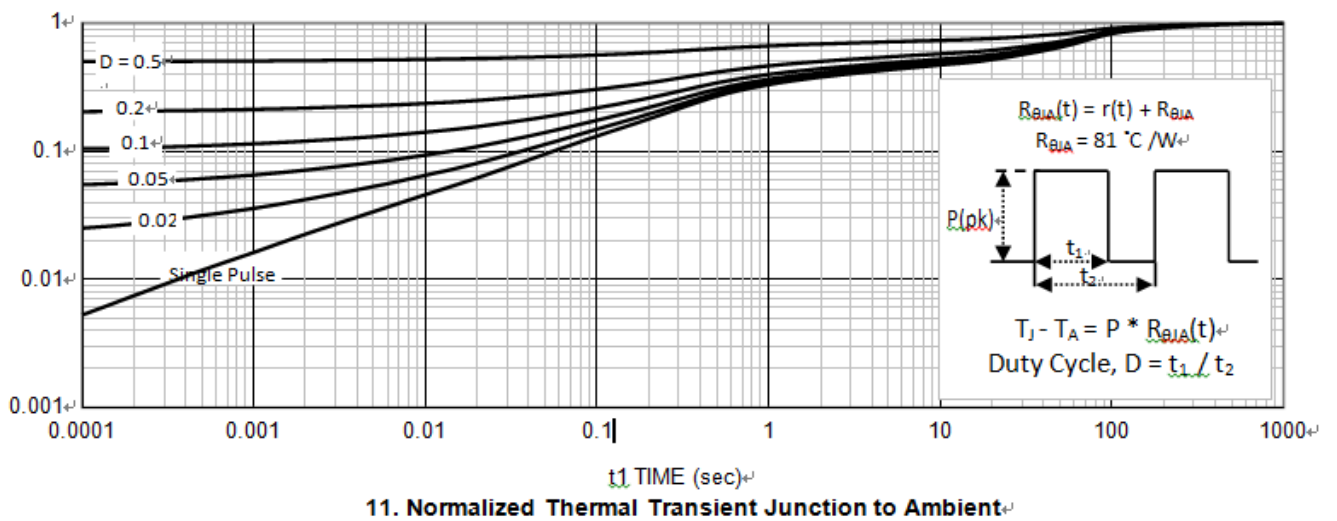
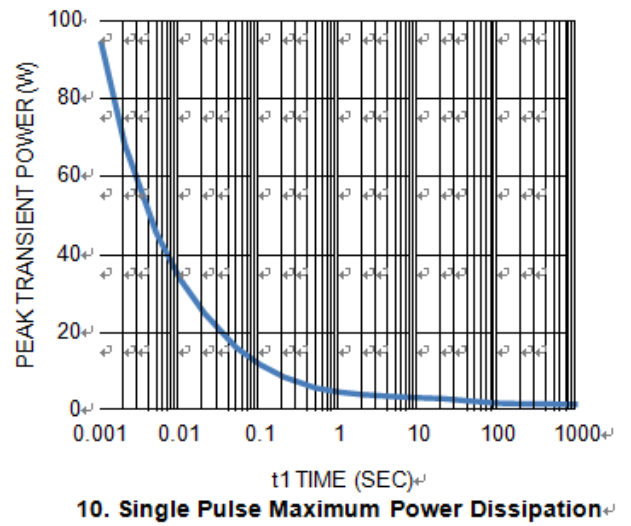
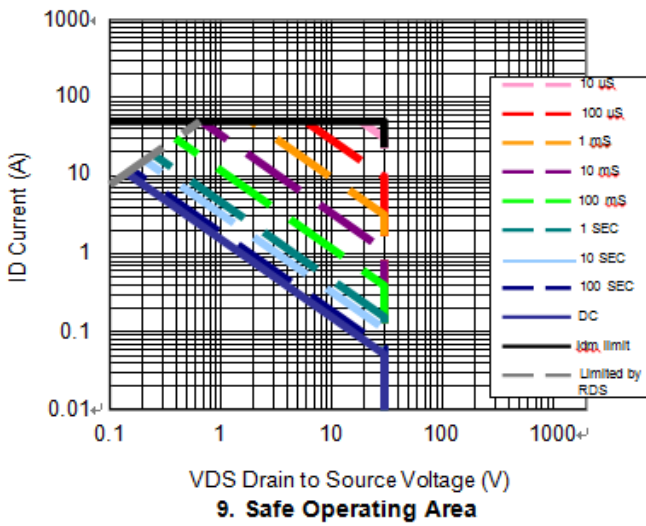
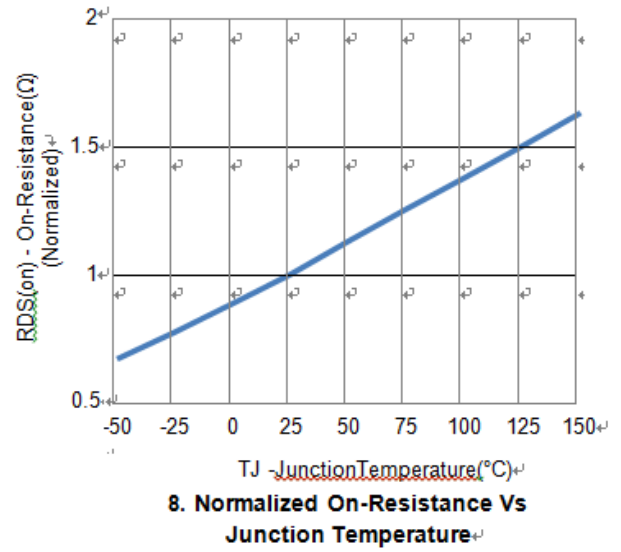
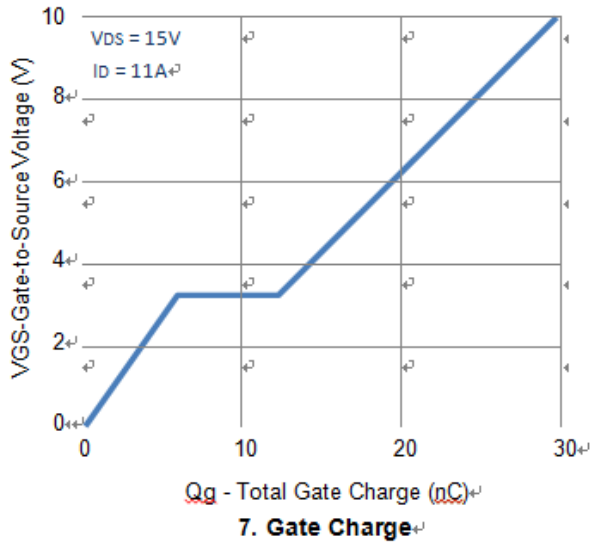


6. Capacitance



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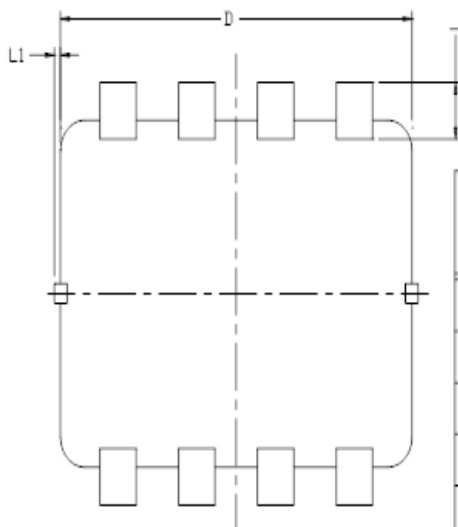
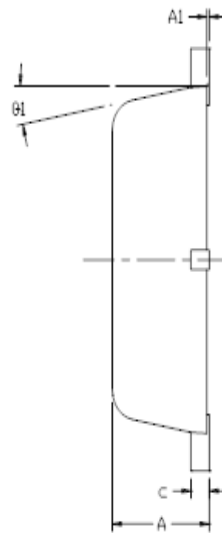
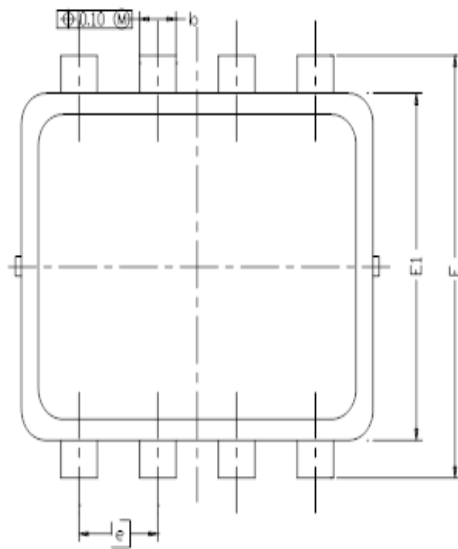
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### Packing Information

DFN3\*3-8L

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Unit: mm

DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.08	0.152	0.25	0.003	0.006	0.010
D	2.90 BSC			0.114 BSC		
E	2.80 BSC			0.110 BSC		
E1	2.30 BSC			0.091 BSC		
e	0.65 BSC			0.026 BSC		
L	0.20	0.375	0.450	0.008	0.0148	0.0177
L1	0	---	0.100	0	---	0.004
θ1	0	10	12	0	10	12



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### Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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